

This Page Is Inserted by IFW Operations
and is not a part of the Official Record

BEST AVAILABLE IMAGES

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images may include (but are not limited to):

- BLACK BORDERS
- TEXT CUT OFF AT TOP, BOTTOM OR SIDES
- FADED TEXT
- ILLEGIBLE TEXT
- SKEWED/SLANTED IMAGES
- COLORED PHOTOS
- BLACK OR VERY BLACK AND WHITE DARK PHOTOS
- GRAY SCALE DOCUMENTS

IMAGES ARE BEST AVAILABLE COPY.

**As rescanning documents *will not* correct images,
please do not report the images to the
Image Problem Mailbox.**

(11) 日本国特許庁 (J P)

(11) 公開特許公報 (A)

(11) 特許公報

特開平 9 - 8 2 0 5

(11) 公報 E 平成 9 年 (1997) : A : C 三

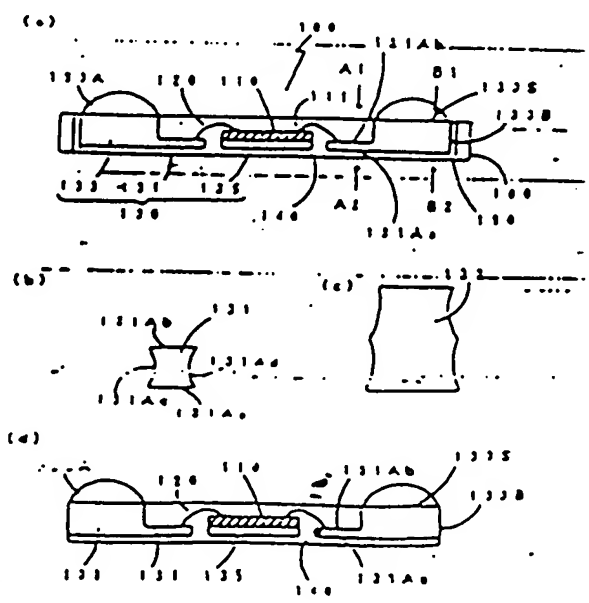
(51) Int. Cl. H01L 23/50 23/12	発明の名称 F I H01L 23/50 23/12	発明の要約 F I H01L 23/50 23/12	発明の要約 F I H01L 23/50 23/12
--------------------------------------	-------------------------------------	-------------------------------------	-------------------------------------

発明の要約 発明の要約 発明の要約 F I 全 5 頁

(11) 出願番号 特願 7 - 170490	(11) 出願人 000002897 大日本印刷株式会社 東京都新宿区市谷加賀町一丁目一番一号
(12) 出願日 平成 7 年 (1995) 6 月 14 日	(13) 発明者 山田 誠一 東京都新宿区市谷加賀町一丁目一番一号 大日本印刷株式会社内
	(14) 発明者 佐々木 誠 東京都新宿区市谷加賀町一丁目一番一号 大日本印刷株式会社内
	(15) 代理人 所澤士 小西 誠典

(54) 【発明の名称】 断層防止型半導体装置

(57) 【要約】 (形証書)
【目的】 多結晶化に対応でき、且つ、フッ素リードの位置ズレや平直性の向上にも対応できる断層防止型半導体装置を提供する。
【構成】 一体的に製造したリードフレーム素子と同じ厚さの外装部材と積層するための凹凸の端子部 133 とを有し、且つ、端子部はインナーリードの外表面においてインナーリードに対して厚み方向に突出して設けられており、端子部の先端部に半田等からなる端子部を設け、端子部を断層防止部から突出させ、端子部の外装部の側面を断層防止部から突出させており、インナーリードは、断面形状が略方形で第 1 面 131Aa、第 2 面 Ab、第 3 面 Ac、第 4 面 Ad の 4 面を有しており、かつ第 1 面はリードフレーム素子と同じ厚さの地の部分の一方の面と同一平面上にあって第 2 面に向をっており、第 3 面、第 4 面はインナーリードの内側に向かって凹んだ形状に形成されている。



(請求項1) 2段ニッチング加工によりインナーリードの厚さがリードフレーム素材の厚さよりも厚みになるように加工されたリードフレームを用いた半導体装置であつて、前記リードフレームは、リードフレーム素材よりも厚みのインナーリードと、該インナーリードに一体的に形成したリードフレーム素材と同じ厚さの外部図層とを有するもので、該外部図層の両面に、且つ、該外部図層はインナーリードの外周面においてインナーリードに対してほぼ90°に直立して設けられており、該外部図層の両面に、該外部図層からなる前記図層を設け、該外部図層を防止層及び保護層から構成させ、該外部図層の外周側の表面に防止層及び保護層から構成されておる、インナーリードは、断面形状が略四方形で第1面、第2面、第3面、第4面の4面を有しており、かつ第1面はリードフレーム素材と同じ厚さの他の部分の一方の面と同一平面上にあって第2面に向合っており、第3面、第4面はインナーリードの内側に向かつて凹んだ形状に形成されていることを特徴とする装置。

【例題2】 2枚ニッティング板によりインターリードの板をリードフレーム素材の板より外面側に外装加工されたリードフレームを用いた導電体基板であつて、前記リードフレームに、リードフレーム素材より外面側のインターリードと、該インターリードに一対的に配置したリードフレーム素材と同じ厚さの外装面材とを積層するための凹凸の嵌合部とを有し、且つ、該嵌合部はインターリードの外周面においてインターリードに対して互う方向に直交して設けられており、該嵌合部の一端を封止用樹脂層から露出させて嵌合部とし、該嵌合部の外周部の側面を封止用樹脂層から露出させており、インターリードは、断面形状が略方形で、第1面、第2面、第3面、第4面の4面を有しており、かつ第1面はリードフレーム素材と同じ厚さの他の部分の一方の面と同一面上にあって第2面に内を合っており、第3面、第4面はインターリードの内側に内かつて凹んだ形状に形成されていることを特徴とする樹脂封止型導電体基板。

(請求項3) 請求項1ないし2において、半導体素子はインナーリード部に設けられ、該半導体素子の電極部はワイヤにてインナーリードと電気的に接続されていることを特徴とする回路装置及び半導体装置。

【請求項4】 請求項3において、リードフレームにダイパッドを有しており、半導体素子がダイパッド上に搭載され、固定されていることを特徴とする半導体装置。

(2) 5) 2) 3) において、リードフレームはダイパッドを挟まないもので、基板端子にインナーリードとともに高強度固定テープにより固定されていることを特徴とする固定防止型基板装置。

(註文例6) 注文1ないし2において、半導体メモリは半導体メモリの電圧値の値をインターリードの第2面

に決定されたものにより決定されており、また価格はその
を決定する要因によりインフレーションの減少と一致する
に調整されていることを保証する必要があることは、これは
a.

(図5-7) 図5-7(1)ないし(2)において、モータ部
にパンプによりインターリードの第2段に固定された
系的にインターリードと連動していることを意味する
本発明の態様である。

(१४०२३५५५)

{ 0 0 0 1 }

(最上上の利用法)は兄弟に、車は不用品の多量に
 に対応と、とつ、アフターリードの拡張型(スニ
)やアフターリードの非拡張型(コブラリチー)の
 の利用法である。リードフレームを用いた車体止型
 車体変型に於て、

{ 0 0 0 2 }

(従来の区画) 従来より用いられている層厚防止型の半導体装置(プラスチックリードフレームパッケージ)は、一面に図15(a)に示されるような構造であり、半導体素子1520を搭載するダイパッド1511の両側の区画との電気的接続を行うためのアウターリード1513、アウターリード1513に一体となったインナーリード1512、該インナーリード1512の先端部と半導体素子1520との電極パッド1521とを電気的に接続するためのワイヤ1530、半導体素子1520を固定して外界からの応力、熱伝から守る樹脂1540面からなっており、半導体素子1520をリードフレームのダイパッド1511の区画に搭載した上、一面に、図15(c)により防止してパッケージにしたりしたので、半導体素子1520の電極パッド1521に対応する数のインナーリード1512を必要とするものであり、そして、このような層厚防止型の半導体装置の製造工程として用いられる(層厚)リードフレームは、一面には図15(b)に示すような構造のもので、半導体素子を搭載するためのダイパッド1511と、ダイパッド1511の両側に設けられた半導体素子を搭載するためのインナーリード1512、該インナーリード1512に連続して外面部との電気的接続を行うためのアウターリード1513、層厚防止する際のダムとなるダムバー1514、リードフレーム1510全体を支持するフレーム(基)部1515等を含んでおり、通常、フパール、42合金(42×ニッケル-銅合金)、銅系合金のような高強度に優れた金属材料を用い、プレス加工もしくはエッチング法により形成されていた。但、図15(c)の(1)は、図15(b)の(1)に示すリードフレーム半導体装置のF1-F2における断面図である。

【0003】このようなリードフレームを具備した増設
禁止型の半導体装置（プラスチックリードフレームパッ
ケージ）において、電子回路の反響低減化の状況とニ
ズをその改善策に照し、小型化および高品質の

て、レーピングの工程や、リードフレームを固定するクランプ工程で、ペタは固定され部分的に厚くなった部分との段差が形成になる場合があるので、エッチングを行うエリアはインナーリード先端の露出加工部分だけにせず大めにとらねばならない。次いで、低温 57°C、比重 4.8 の水酸化第二硫酸塩を用いて、スプレーで 2.5 kg/cm² にて、レジストパターンが形成されたリードフレームを 1110 の溶液をエッチングし、ペタは（平定状）に固定された第一の凹部 1150 の底面がリードフレーム露出部の 2/3 程度に達した時点でエッチングを止めた。（図 11 (b)）

上記第 1 回目のエッチングにおいては、リードフレームは 1110 の溶液から同時にエッチングを行ったが、必ずしも同時にエッチングする必要はない。本実施例のように、第 1 回目のエッチングにおいてリードフレームは 1110 の溶液から同時にエッチングする理由は、露出部からエッチングすることにより、固定する第 2 回目のエッチング時間を短縮するため、レジストパターン 920B 露出部のみの露出エッチングの場合と比べ、第 1 回目エッチングと第 2 回目エッチングのトータル時間が短縮される。次いで、第一の凹部 1130 側の露出された第一の凹部 1500 にエッチング液を 1180 としてエッチング液のあるホットメルト型

フックス（ブレイク、元ニックス社のフックス、型番 MR-WB6）を、ダイコータを用いて、塗布し、ペタは（平定状）に固定された第一の凹部 1150 に埋め込んだ。レジストパターン 1120A 上にもエッチング液 1180 に塗布された状態とした。（図 11 (c)）

エッチング液 1180 を、レジストパターン 1120A 上全面に塗布する必要はないが、第一の凹部 1150 を含む一面にのみ塗布することにした。図 11 (c) に示すように、第一の凹部 1150 とともに、第一の凹部 1130 側全面にエッチング液 1180 を塗布した。本実施例で使用したエッチング液 1180 は、アルカリ性水素のフックスであるが、基本的にエッチング液に耐性があり、エッチング時に露出部の腐食性のあるものが、析出して、特に、上記フックスに固定された U.V. 硬化型のものでは無い。このようにエッチング液 1180 をインナーリード先端部の露出部を形成するためのパターンが形成された露出部の露出された第一の凹部 1150 に塗布することにより、露出部のエッチング時に第一の凹部 1150 が露出されて太くならないようにしているとともに、露出部をエッチング加工に耐える腐食性のある性質をしており、スプレーを高く（2.5 kg/cm² 以上）とすることができ、これによりエッチングが露出部方向に進行しやすくなる。この後、第 2 回目のエッチングを行う。ペタは（平定状）に固定された第二の凹部 1160 露出部からリードフレーム露出部 1110 をエッチングし、露出させ、

インナーリード先端部 131A を形成した。（図 11 (c)）

第 1 回目のエッチング加工にて作成された、リードフレーム面に平行なエッチング形成面は露出であるが、この面を露出 2 面はインナーリード側にへこんだ凹部である。次いで、洗浄、エッチング液 920B の露出レジスト（レジストパターン 1120A、1120B）の露出を行い、インナーリード先端部 131A が露出加工された図 9 (a) に示すリードフレーム 130A を得た。エッチング液 920B とレジスト（レジストパターン 1120A、1120B）の露出に露出したトリウム水素塩により露出部は露出した。

（0014）上記、図 11 に示すリードフレームの露出状態は、本実施例に用いられる、インナーリード先端部を露出に形成したリードフレームをエッチング加工により露出する状態で、特に、図 11 に示す、インナーリード先端部の第 1 凹部 131A を露出部以外の露出の部分と同一面に、第 2 凹部 131B と対向させて形成し、且つ、第 3 凹部 131C、第 4 凹部 131D をインナーリードの内側に向かって凹んだ形状にするエッチング加工方法である。試述する本実施例の露出部を露出するようにパンプを用いて露出部をインナーリードの第 2 凹部 131B に露出し、インナーリードと露出部に露出する場合には、

第 2 凹部 131B をインナーリード側に凹んだ形状に形成した方がパンプ露出部の露出面積が大きくなる。

図 12 に示すエッチング加工方法が知られる。図 12 に示すエッチング加工方法は、第 1 回目のエッチング工程までは、図 11 に示す方法と同じであるが、エッチング液 1180 を第二の凹部 1160 側に埋め込んだ後、第一の凹部 1150 側から第 2 回目のエッチングを行い、露出部を露出させている。図 12 第 1 回目のエッチングにて、第二凹部 1140 からのエッチングを露出に留めておく。図 12 に示すエッチング加工方法によって露出したリードフレームのインナーリード先端部の露出形状は、図 6 (b) に示すように、第 2 凹部 131B がインナーリード側にへこんだ凹部になる。

（0015）図 11、図 12 に示すエッチング加工方法のように、エッチングを 2 段階に分けて行うエッチング加工方法を、一般には 2 段階エッチング加工方法という。本実施例に有利な加工方法である。本実施例に用いた図 9 (a) に示す、リードフレーム 130A の露出部においては、露出部をエッチング加工することにより部分的にリードフレーム露出部を露出したが、露出部を露出した部分に露出しており、リードフレーム露出部を露出した部分に露出している。図 11、図 12 に示す、上記の方法においては、インナーリード先端部 131A の露出加工は、第二の凹部 1160 の露出と、露出部には用いられるインナーリード先端部の露出に露出されるもので、例えば、露出部（50 μm

IIは黒色版、J50は減感用テープである。写真感光
の系は写真において、主感材をJ10に、バインダ
J11によりインターリードJ31の厚2度J31を
に固定され、実質的にインターリードJ31と固定して
いる。リードフレームJ30は、図10(a)、図11
(b)に示す形状のもので、図11に示す二つのピンは
互によりばねを付けたものを用いている。図13(b)

(b)に示すように、インターリード331の位置は
W1A、W2A (約100μm) ともこの部分のほぼ
10 万回の間のW4よりも大きくなっており、まづ、イン
ターリード331の第2面331Abはインターリー
ドの内部に向かって凹んだ形状で、第1面331Aが二
層であることより、インターリードの位置化に対応さ
るとともに、インターリード331の第2面331Ac
において、ニッケルとバンプにて電気的に接続する
際には、図13(c) (b) のように接続がし易いもの
としている。また、ニッケル331の場合、第1面1や第
2面の場合と同様に、ニッケル33100と第2面331
の電気的な接続は、第1面331Aの面に付けられたニ
20 ッケルを介する第1面331Aを介してプリント配
線へ接続することにより行われる。
(002) 第2面331のニッケル位置は、第1面1のニ
ッケルの場合と異なり、図12に示すニッチングによ
り形成されたリニードスリットを用いたものであ

が、ニズ体基は母体の製法にはほぼ同じ工程である。異なる点に、高純度のニズ体基製造の場合にはニズ体基をインターリードに固定した状態でワイヤボンディングを行い、その後封止しているのに対し、本発明例①のニズ体基の場合は、ニズ体基と③④モイネーターリード⑤⑥⑦⑧にパンプを介して固定するための接続した状態で封止されている点である。この封止後のプロセスに、ニズ体基部分の切断、異分子鎖の形成に、本発明例①のニズ体基造の場合と同じである。

(0024) 図6 (a) に示す図例3の半導体装置の断面図は、半導体装置の断面図である。図6 (a) に示す断面図は、図例3の半導体装置において、半導体の表面からなる導電膜を設けず、導電膜の面を区別導電膜として設けているものである。図例3を参照して半導体111の上面111Bを上面に露出しているため、チャンネルでの電荷のテクニックがし易い構造となっている。更にこの導電膜111の上面111Bを絶縁膜とすると、素子からテクニックし易い構造とすることもできる。

(1025) は、式(4)の原理防止型回路を
 図7(a)は式(4)の原理防止型回路の
 断面図であり、図7(b)は図7(a)のA7-A
 8におけるインターリード部の断面図で、図6(c)は
 図6(a)の67-98における端子部Eの断面図であ
 る。図7(a)の原理防止型回路の原理防止部1とは
 同じとなる。図に示した、図7中、400は導電
 性部、410は導電性部、411はパッド、430は

190
 260
 270
 350
 470
 1110
 1120A, 1120B
 1130
 1140
 1150
 1160
 1170
 1180
 1320B, 1320C, 1320D
 1321B, 1321C, 1321D
 1331B, 1331C, 1331D
 1331A, 2

1331A, b
 1410
 1420
 1430
 1440
 1510
 1511
 1512
 1512A
 1513
 1514
 1515
 1520
 1521
 1530
 1540

ードフレーム部

イニング部

ードフレーム部

オートレジスト

ジストパターン

ンナーリード

ードフレーム

イパッド

ンナーリード

ンナーリード先頭部

クターリード

ムバー

レーン部 (内部)

部品表示

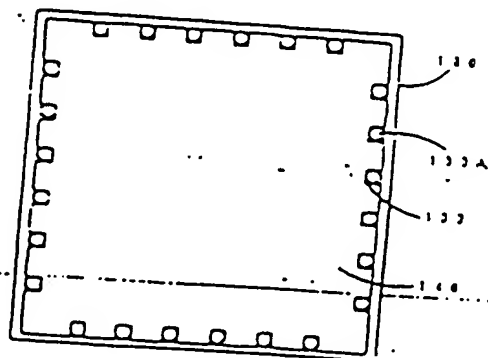
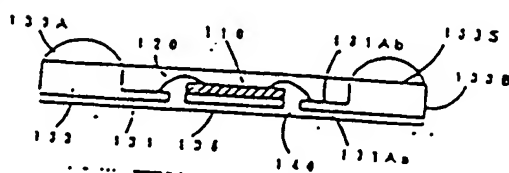
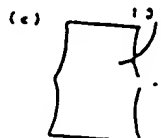
部 (パッド)

イ

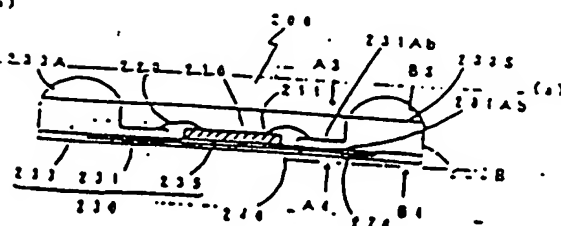
止用部

44-38861-2205

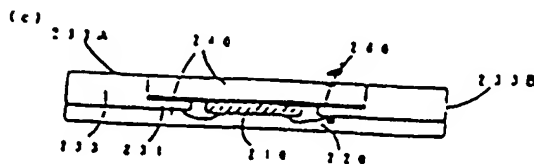
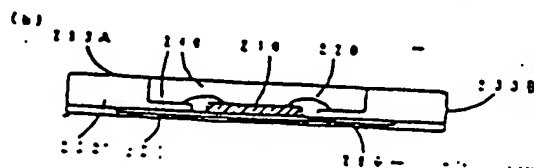
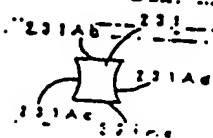
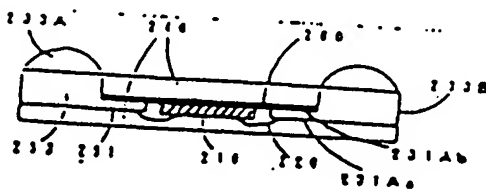
(2)



(24)



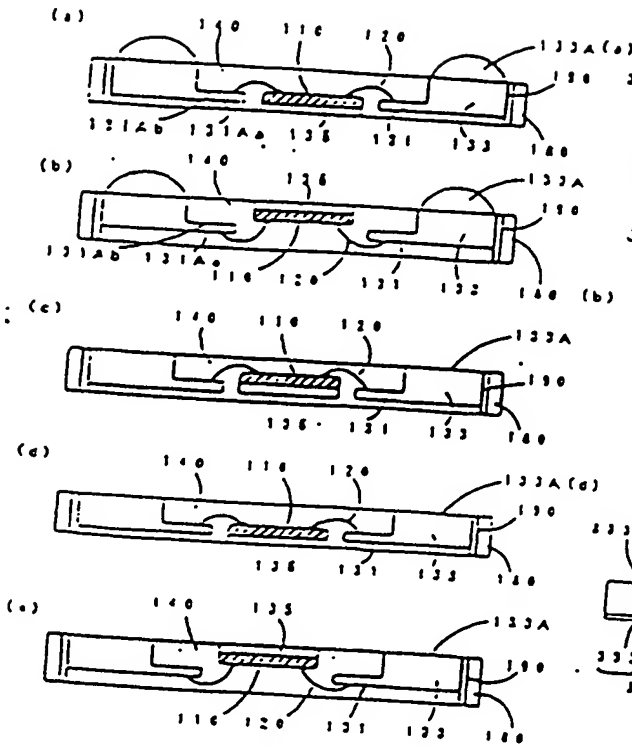
(25)



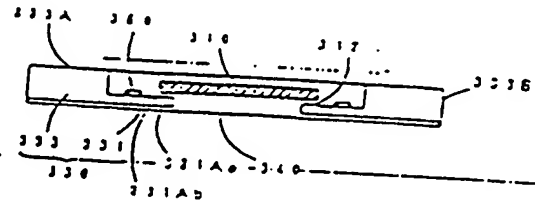
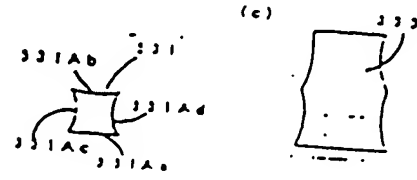
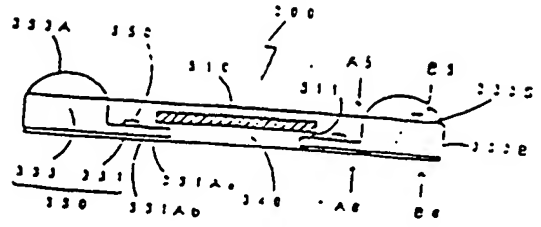
(12)

图 9-2205

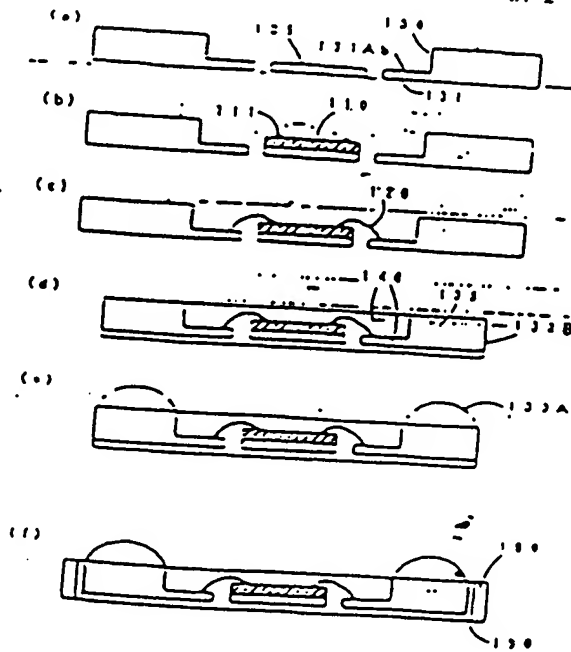
(23)



(26)



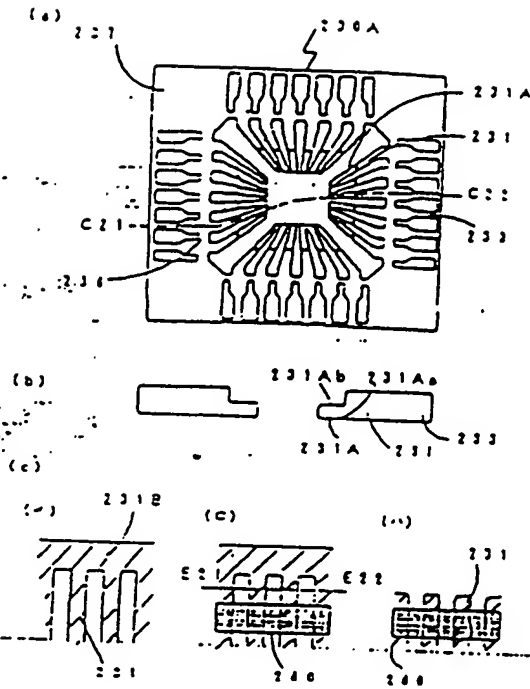
(25)



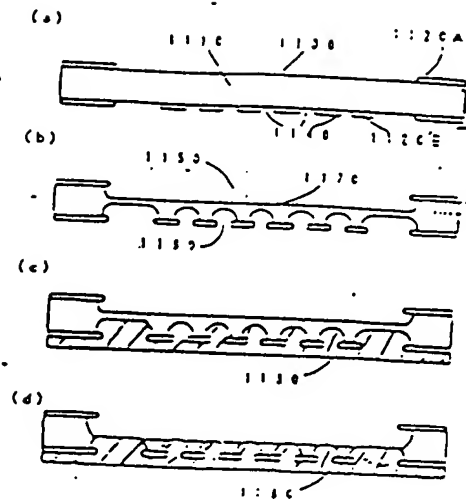
(14)

PRE9-6205

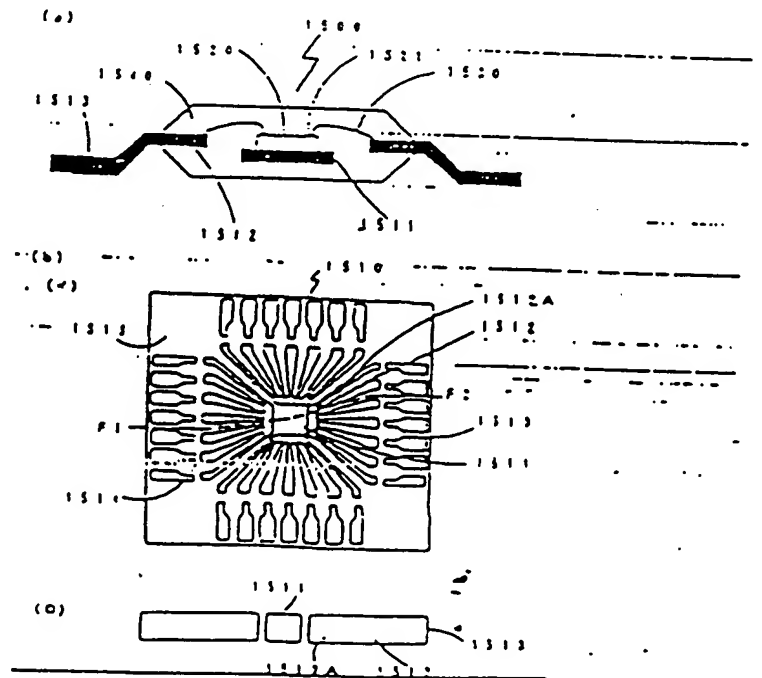
(210)



(212)



(215)



Japanese Patent Laid-Open Publication No. Heisei 9-8205

[TITLE OF THE INVENTION]

RESIN-ENCAPSULATED SEMICONDUCTOR DEVICE

5

[CLAIMS]

1. A resin-encapsulated semiconductor device using
a lead frame which is shaped in accordance with a two-step
etching process to a body wherein a thickness of inner
10 leads is less than that of the lead frame blank,
comprising:

inner leads having the thickness less than that of the
lead frame blank; and

terminal columns integrally connected to the inner
15 leads and having the same thickness with the lead frame
blank, the terminal columns possessing a column-shaped
configuration which is adapted to be electrically connected
to an external circuit, the terminal columns being disposed
outside of the inner leads in a manner such that they are
20 coupled to the inner leads in a direction orthogonal to the
thickness-wise direction thereof, the terminal columns
having terminal portions arranged on top ends thereof, the
terminal portions being made of solders, etc. and exposed
to the outside beyond a resin encapsulate, each inner lead
25 possessing a rectangular cross-section and having four

surfaces including a first surface, a second surface, a third surface and a fourth surface, the first surface being flushed with one surface of a remaining portion of the inner lead having the same thickness with the lead frame blank while being opposed to the second surface, and each
5 of the third and fourth surfaces having a concave shape depressed toward the inside of the inner lead.

2. A resin-encapsulated semiconductor device using
10 a lead frame which is shaped in accordance with a two-step etching process to a body wherein a thickness of inner leads is less than that of the lead frame blank, comprising:

inner leads having the thickness less than that of the
15 lead frame blank; and

terminal columns integrally connected to the inner leads and having the same thickness with the lead frame blank, the terminal columns possessing a column-shaped configuration which is adapted to be electrically connected
20 to an external circuit, the terminal columns being disposed outside of the inner leads in a manner such that they are coupled to the inner leads in a direction orthogonal to the thickness-wise direction thereof, portions of top ends of the terminal columns being exposed to the outside beyond a
25 resin encapsulate, each inner lead possessing a rectangular

cross-section and having four surfaces including a first surface, a second surface, a third surface and a fourth surface, the first surface being flushed with one surface of a remaining portion of the inner lead having the same thickness with the lead frame blank, while being opposed to the second surface, and each of the third and fourth surfaces having a concave shape depressed toward the inside of the inner lead.

3. The resin-encapsulated semiconductor device as claimed in claims 1 or 2, wherein a semiconductor chip is received inward of the inner leads, and electrodes of the semiconductor chip are electrically connected to the inner leads through wires, respectively.

4. The resin-encapsulated semiconductor device as claimed in claim 3, wherein the lead frame has a die pad, and the semiconductor chip is mounted onto the die pad.

5. The resin-encapsulated semiconductor device as claimed in claim 3, wherein the lead frame does not have a die pad, and the semiconductor chip is fastened to the inner leads using a reinforcing fastener tape.

6. The resin-encapsulated semiconductor device as

claimed in claims 1 or 2, wherein the semiconductor chip is fastened by means of insulating adhesive to the second surfaces of the inner leads on one surface thereof on which the electrodes are located, and the electrodes of the semiconductor chip are electrically connected to the first surfaces of the inner leads through wires, respectively.

7. The resin-encapsulated semiconductor device as claimed in claims 1 or 2, wherein the semiconductor chip is fastened to the second surfaces of the inner leads by bumps thereby to be electrically connected to the inner leads.

[DETAILED DESCRIPTION OF THE INVENTION]

[FIELD OF THE INVENTION]

The present invention relates to a resin-encapsulated semiconductor device capable of meeting the requirement for an increase in the number of terminals and resolving problems which are caused in association with position shift and coplanarity of an outer lead.

[DESCRIPTION OF THE PRIOR ART]

FIG. 15(a) shows the configuration of a generally known resin-encapsulated semiconductor device (a plastic lead frame package). The shown resin-encapsulated semiconductor device includes a die pad 1511 having a

semiconductor chip 1520 mounted thereon, outer leads 1513 to be electrically connected to the associated circuits, inner leads 1512 formed integrally with the outer leads 1513, bonding wires 1530 for electrically connecting the tips of the inner leads 1512 to the bonding pad 1521 of the semiconductor chip 1520, and a resin 1540 encapsulating the semiconductor chip 1520 to protect the semiconductor chip 1520 from external stresses and contaminants. This resin-encapsulated semiconductor device, after mounting the semiconductor chip 1520 on the bonding pad 1521, is manufactured by encapsulating the semiconductor chip 1520 with the resin. In this resin-encapsulated semiconductor device, the number of the inner leads 1512 is equal to that of the bonding pads 1521 of the semiconductor chip 1520. And, FIG. 15(b) shows the configuration of a monolayer lead frame used as an assembly member of the resin-encapsulated semiconductor device shown in FIG. 15a. Such a lead frame includes the bonding pad 1511 for mounting the semiconductor chip, the inner leads 1512 to be electrically connected to the semiconductor chip, the outer lead 1513 which is integral with the inner leads 1512 and is to be electrically connected to the associated circuits. This also includes dam bars 1514 serving as a dam when encapsulating the semiconductor chip with the resin, and a frame 1515 serving to support the entire lead frame 1510.

Such a lead frame is formed from a highly conductive metal such as a cobalt, 42 alloy (a 42% Ni-Fe alloy), copper-based alloy by a pressing working process or an etching process. FIG. 15(b)(D) is a cross-sectional view taken along the line F1-F2 of FIG. 15(b)(1).

Recently, there has been growing demand for the miniaturization and reduction in thickness of resin-encapsulated semiconductor device employing lead frames like the lead frame (plastic lead frame package) and the increase of the number of terminals of resin-encapsulated semiconductor package as electronic apparatuses are miniaturized progressively and the degree of the integration of semiconductor device increase progressively. Thus, recent resin-encapsulated semiconductor package, particularly quad plate package (QFPs) and thin quad flat packages (TQFPs) have each a greatly increased number of pins.

Lead frames having inner leads arranged at small pitches among lead frames for semiconductor packages are fabricated by a photolithographic etching process, while lead frames having inner leads arranged at comparatively large pitches among lead frames for semiconductor packages are fabricated by press working. However, lead frames having a large number of fine inner leads to be used for forming semiconductor packages having a large number of

pins are fabricated by subjecting a blank of a thickness on the order of 0.25 mm to an etching process, not a press working.

5 The etching process for forming a lead frame having fine inner leads will be described hereinafter with reference to FIG. 14. First, a copper alloy or 42 alloy thin sheet of a thickness on the order of 0.25 mm (a lead frame blank 1410) is cleaned perfectly (FIG. 14(a)). Then, a photoresist, such as a water-soluble casein photoresist
10 containing potassium dichromate as a sensitive agent, is spread in photoresist films 1420 over the major surfaces of the thin film as shown in FIG. 14(b).

15 Then, the photoresist films are exposed, through a mask of a predetermined pattern, to light emitted by a high-pressure mercury lamp, and the thin sheet is immersed in a developer for development to form a patterned photoresist film 1430 as shown in FIG. 14(c). Then, the thin sheet is subjected, when need be, to a hardening process, a washing process and such, and then an etchant
20 containing ferric chloride as a principal component is sprayed against the thin sheet 1410 to etch through portions of the thin sheet 1410 not coated with the patterned photoresist films 1020 so that inner leads of predetermined sizes and shapes are formed as shown in FIG.
25 14(d).

Then, the patterned resist films are removed, the patterned thin sheet 1410 is washed to complete a lead frame having the inner leads of desired shapes as shown in FIG. 14(e). Predetermined areas of the lead frame thus formed by the etching process are silver-plated. After being washed and dried, an adhesive polyimide tape is stuck to the inner leads for fixation, predetermined tab bars are bent, when need be, and the die pad depressed. In the etching process, the etchant etches the thin sheet in both the direction of the thickness and directions perpendicular to the thickness, which limits the miniaturization of inner lead pitches of lead frames. Since the thin sheet is etched from both the major surfaces as shown in FIG. 14 during the etching process, it is said, when the lead frame has a line-and-space shape, that the smallest possible intervals between the lines are in the range of 50 to 100% of the thickness of the thin sheet. From the viewpoint of forming the outer lead having a sufficient strength, generally, the thickness of the thin sheet must be about 0.125 mm or above. Furthermore, the width of the inner leads must be in the range of 70 to 80 μ m for successful wire bonding. When the etching process as illustrated in FIG. 14 is employed in fabricating a lead frame, a thin sheet of a small thickness in the range of 0.125 to 0.15 mm is used and inner leads are formed by etching so that the

fine tips thereof are arranged at a pitch of about 0.1 mm.

However, recent miniature resin-encapsulated semiconductor package requires inner leads arranged
5 pitches in the range of 0.13 to 0.15 mm, far smaller than 0.165 mm. When a lead frame is fabricated by processing thin sheet of a reduced thickness, the strength of the outer leads of such a lead frame is not large enough
10 withstand external forces that may be applied thereto in the subsequent processes including an assembling process and a chip mounting process. Accordingly, there is a limit to the reduction of the thickness of the thin sheet to enable the fabrication of a minute lead frame having fine leads arranged at very small pitches by etching.

15 An etching method previously proposed to overcome such difficulties subjects a thin sheet to an etching process to form a lead frame after reducing the thickness of portions of the thin sheet corresponding to the inner leads of the lead frame by half etching or pressing to form
20 the fine inner leads by etching without reducing the strength of the outer leads. However, problems arise in accuracy in the subsequent processes when the lead frame is formed by etching after reducing the thickness of the portions corresponding to the inner leads by pressing; for
25 example, the smoothness of the surface of the plated areas

is unsatisfactory, the inner leads cannot be formed in a flatness and a dimensional accuracy required to clamp the lead frame accurately for bonding and molding, and a platemaking process must be repeated twice making the lead fabricating process intricate. It is also necessary to repeat a platemaking process twice when the thickness of the portions of the thin sheet corresponding to the inner leads is reduced by half etching before subjecting the thin sheet to an etching process for forming the lead frame, which also makes the lead frame fabricating process intricate. Thus, this previously proposed etching method has not yet been applied to practical lead frame fabricating processes.

15 (SUBJECT MATTERS TO BE SOLVED BY THE INVENTION)

On the other hand, because a pitch among inner leads is made narrow as the number of terminals is increased, it is considered important to know whether a problem is caused or not in association with position shift or coplanarity of an outer lead when implementing a chip mounting process. Accordingly, the present invention has been made in an effort to solve the problems occurring in the related art, and an object of the present invention is to provide a resin-encapsulated semiconductor device capable of meeting the requirement for an increase in the number of terminals

and resolving problems which are caused in association with position shift and coplanarity of an outer lead.

[MEANS FOR SOLVING THE SUBJECT MATTERS]

5 According to one aspect of the present invention, there is provided a resin-encapsulated semiconductor device using a lead frame which is shaped in accordance with a two-step etching process to a body wherein a thickness of inner leads is less than that of the lead frame blank, comprising: inner leads having the thickness less than that of the lead frame blank; and terminal columns electrically connected to the inner leads and having the same thickness as the lead frame blank, the terminal columns positioned in a column-shaped configuration which is adapted to be electrically connected to an external circuit, the terminal columns being disposed outside of the inner leads in a manner such that they are coupled to the inner leads in a direction orthogonal to the thickness-wise direction thereof, the terminal columns having terminal portions arranged on top ends thereof, the terminal portions being made of solders, etc. and exposed to the outside beyond the resin encapsulate, outer surfaces of the terminal columns also being exposed to the outside beyond the resin encapsulate, each inner lead possessing a rectangular cross-section and having four surfaces including a

10

15

20

25

surface, a second surface, a third surface and a fourth surface, the first surface being flushed with one surface of a remaining portion of the inner lead having the same thickness with the lead frame blank while being opposed to the second surface, and each of the third and fourth surfaces having a concave shape depressed toward the inside of the inner lead.

According to another aspect of the present invention there is provided a resin-encapsulated semiconductor device using a lead frame which is shaped in accordance with a two-step etching process to a body wherein a thickness of inner leads is less than that of the lead frame blank comprising: inner leads having the thickness less than that of the lead frame blank; and terminal columns integrally connected to the inner leads and having the same thickness with the lead frame blank, the terminal columns possessing a column-shaped configuration which is adapted to be electrically connected to an external circuit, the terminal columns being disposed outside of the inner leads in a manner such that they are coupled to the inner leads in a direction orthogonal to the thickness-wise direction thereof, portions of top ends of the terminal columns being exposed to the outside beyond a resin encapsulate, outer surfaces of the terminal columns also being exposed to the outside beyond the resin encapsulate, each inner lead

possessing a rectangular cross-section and having four surfaces including a first surface, a second surface, a third surface and a fourth surface, the first surface being flushed with one surface of a remaining portion of the inner lead having the same thickness with the lead frame blank while being opposed to the second surface, and each of the third and fourth surfaces having a concave shape depressed toward the inside of the inner lead.

According to another aspect of the present invention, a semiconductor chip is received inward of the inner leads, and electrodes (pads) of the semiconductor chip are electrically connected to the inner leads through wires, respectively. According to another aspect of the present invention, the lead frame has a die pad, and the semiconductor chip is mounted onto the die pad. According to another aspect of the present invention, the lead frame does not have a die pad, and the semiconductor chip is fastened to the inner leads using a reinforcing fastener tape. According to still another aspect of the present invention, the semiconductor chip is fastened by means of insulating adhesive to the second surfaces of the inner leads on one surface thereof on which the electrodes are located, and the electrodes of the semiconductor chip are electrically connected to the first surfaces of the inner leads through wires, respectively. According to yet still

another aspect of the present invention, the semiconductor chip is fastened to the second surfaces of the inner leads by bumps thereby to be electrically connected to the inner leads. In the above descriptions, in the case that the terminal columns have terminal portions which are arranged on top ends of the terminal columns, with the terminal portions made of solders, etc. and exposed to the outside beyond the resin encapsulate, while it is the norm that the terminal portions comprising the solders, etc. are exposed to the outside beyond the resin encapsulate, it is not necessarily required for the terminal portions to be projected beyond the resin encapsulate. Moreover, while it is possible to use the outside surfaces of the terminal columns while they are not encapsulated by the resin encapsulate and they are exposed to the outside, the outside surfaces of the terminal columns which are not encapsulated by the resin encapsulate, can be covered by a protective frame using adhesive, etc.

20 [WORKING FUNCTIONS]

The resin-encapsulated semiconductor device in accordance with the present invention can meet a demand for an increase in the number of terminals. At the same time, in the resin-encapsulated semiconductor device, because the forming process of the outer leads as in the case of using

a mono-layered lead frame shown in FIG. 13(b) is not required, it is possible to provide a semiconductor device in which no problems are caused in association with position shift and coplanarity of the outer leads. More particularly, the use of a multi-pinned lead frame shaped in a manner that inner leads have a thickness less than that of the lead frame blank by a two-step etching process, that is, the inner leads are arranged at a fine pitch, can meet a demand for an increase in the pin number of the semiconductor device. Furthermore, by using the lead frame which is fabricated by a two-step etching process as will be described later with reference to FIG. 1, the second surface of each inner lead has coplanarity, and is excellent in wire-bonding property. In addition, since the first surface of the inner lead is also a flat surface and the third and fourth surfaces are depressed toward the inside of the inner lead, the inner leads are stable and coplanarity width upon wire bonding process can be enlarged.

[EMBODIMENTS]

Embodiments of the resin-encapsulated semiconductor device in accordance with the present invention will now be described with reference to the attached drawings. First, a resin-encapsulated semiconductor device in accordance

with a first embodiment of the present invention described hereinafter with reference to FIGs. 1. FIG. 1(a) is a cross-sectional view of the encapsulated semiconductor device according to the embodiment of the present invention. FIG. 1(b) is a sectional view of an inner lead taken along the line of FIG. 1(a), and FIG. 1(c) is a cross-sectional view of a terminal column taken along the line B1-B2 of FIG. 1. Moreover, FIG. 2(a) is a perspective view of the encapsulated semiconductor device according to the embodiment of the present invention, FIG. 2(b) is a view of the resin-encapsulated semiconductor device of FIG. 2(a), and FIG. 2(c) is a bottom view of the encapsulated semiconductor device of FIG. 2(a). In FIGs. 1 and 2, a drawing reference numeral 100 represents a resin-encapsulated semiconductor device, 110 a semiconductor chip, 111 electrodes (pads), 120 wires, 130 a lead frame, 131 inner leads, 131Aa a first surface, 131Ab a second surface, 131Ac a third surface, 131Ad a fourth surface, 132 terminal columns, 133A terminal portions, 133B side surfaces, 133S a top surface, 135 a die pad, and 140 resin encapsulate.

In the resin-encapsulated semiconductor device according to the first embodiment, as shown in FIG. 1, the semiconductor chip 110 is placed inward of the

leads 131. As can be readily seen from FIG. 1(a), the semiconductor chip 110 is mounted on the die pad 133 at one surface thereof which is opposed to the other surface thereof where the electrodes pads 111 of the semiconductor chip 110 are arranged. Each electrode pad 111 is electrically connected to the second surface 131a of the inner lead 131 through the wire 120. The electrical connection between the resin-encapsulated semiconductor device 100 of this embodiment and an external circuit is achieved by mounting the resin-encapsulated semiconductor device 100 via the terminal portions 133A each being made of a semi-spherical solder, on a printed circuit substrate, with the terminal portions 133A located on the top surfaces 133S of the terminal columns 133, respectively. In the resin-encapsulated semiconductor device of the first embodiment of the present invention, it is not necessarily required to provide a protective frame 180, and instead, a structure, as shown in FIG. 1(d), in which no protective frame is used can be adopted.

The lead frame 130 used in the semiconductor device 100 according to the first embodiment is made of a 42% nickel-iron alloy. Therefore, the lead frame 130A which has a contour as shown in FIG. 9(a) and is shaped by an etching process, is used as the lead frame 130. The lead frame 130 has inner leads 131 which are shaped to have a

thickness less than that of the terminal columns 133 or other portions. Dam bars 136 serve as a dam when encapsulating the semiconductor chip 110 with a resin. Moreover, although the lead frame 130A which is processed by etching to have the contour as shown in FIG. 9A is used in this embodiment, the lead frame is not limited to such a contour because portions except the inner leads 131 and the terminal columns 133 are not necessary. The inner leads 131 have a thickness of 40 μ m whereas the portions of the lead frame 130 other than the inner leads 131 have a thickness of 0.15 mm which corresponds to the thickness of the lead frame blank. The other portions of the lead frame 130 except the inner leads 131 may not have the thickness of 0.15 mm, but have a thickness of 0.125 mm-0.50 mm which is thinner. The tips of the inner leads 131 have a small pitch of 0.12 mm so as to achieve an increase in the number of terminals for semiconductor devices. The second face 131Ab of the inner lead 131 has a substantially flat profile so as to allow an easy wire bonding thereon. Also, as shown in FIG. 1(b), because the third and fourth faces 131Ac and 131Ad have a concave shape which is depressed toward the inside of the associated inner lead, a high strength can be obtained even though the second face (wire bonding surface) 131Ab is narrowed.

In the present embodiment, since twisting does not

occur in the inner leads 131 irrespective of whether the inner leads 131 is long or not. The inner leads having the contour, as shown in FIG. 9(a), in which the tips of the inner leads 131 are separated one from another, are prepared by the etching process, and the inner leads are resin-encapsulated after mounting the semiconductor chip thereon as will be described later. However, where the inner leads 131 are long in their length and have a tendency for the generation of twisting therein, it is impossible to fabricate the lead frame by etching to have the contour as shown in FIG. 9(a). Therefore, after etching the lead frame in a state where the tips of the inner leads are fixed to the connecting portion 131B as shown in FIG. 9(c)(1), the inner leads 131 are fixed with the reinforcing tape 160 as shown in FIG. 9(c)(2). Then, the connecting portions 131B which are not necessary in the fabrication of the resin-encapsulated semiconductor device are removed by a press as shown in FIG. 9(c)(3), and a semiconductor device is then mounted on the lead frame.

Hereinafter, a method for the fabrication of the resin-encapsulated semiconductor device will now be described with reference to FIG. 8. First, the lead frame 130A, as shown in FIG. 9(a), which is shaped by the etching process as will be described later, is prepared such that the second surfaces 131Ab of the inner leads 131 are

directed upward (FIG. 8(a)).

Then, the semiconductor chip 110 is mounted onto the die pad 135 such that the surfaces of the semiconductor chip 110 on which the electrodes 111 are arranged, are
5 directed upward (FIG. 8(b)).

Next, after the semiconductor chip 110 is fastened onto the die pad 135, the electrodes 111 of the semiconductor chip 110 and the second surfaces 131ab of the inner leads 131 are bonded with each other using wires 120
10 (FIG. 8(c)).

Subsequently, encapsulation is carried out with the conventional resin encapsulate 140. Thereafter, unnecessary portions of the lead frame 130 which are protruded from the resin encapsulate 140 are cut by a press
15 to form terminal columns 133 and also the side surfaces 133b of the terminal columns 133 (FIG. 8(d)).

Then, the dam bars 136, the frame portions 137, etc. of the lead frame 130A as shown in FIG. 9 are removed. Next, the terminal portions 133A each made of the semi-
20 spherical solder are arranged on the outer surface of each terminal column 133 to fabricate a resin-encapsulated semiconductor device (FIG. 8(e)).

Thereafter, the protective frame 180 is arranged by means of adhesive around an entire outer surface of the
25 resultant structure in such a manner that the side surfaces

of the terminal columns 133 are covered thereby FIG. 6(f)). At this time, the protective frame 180 functions to reinforce the semiconductor device. In other words, the protective frame 180 serves to prevent moisture from
5 leaking into a gap between the resin encapsulate and the terminal columns due to the fact that the side surfaces of the terminal columns are exposed to the outside, whereby a crack is not formed in the semiconductor device and the breakage of the semiconductor device is avoided. However,
10 persons skilled in the art will readily appreciate that it is not necessarily required to provide the protective frame 180. Also, when such an encapsulating process by the resin is carried out using a desired mold, the encapsulating process is implemented in a state wherein the outer side
15 surfaces of the terminal columns of the lead frame are somewhat protruded out of the resin encapsulate.

A method for etching the lead frame of the first embodiment will now be described in conjunction with the attached drawings. FIG. 11 is of cross-sectional views
20 respectively illustrating sequential steps of the etching process for the lead frame of the first embodiment. In particular, the cross-sectional views of FIG. 1 correspond to a cross section taken along the line D1-D2 of FIG. 9(a). In FIG. 11, the reference numeral 1110 denotes a lead frame
25 blank, 1120A and 1120B resist patterns, 1130 first opening,

1140 second openings, 1150 first concave portions, 1160 second concave portions, 1170 flat surfaces, and 1180 an etch-resistant layer. First, a water-soluble casein resist using potassium dichromate as a sensitive agent is coated
5 over both surfaces of the lead frame blank 1110 made of a 42% nickel-iron alloy and having a thickness of about 0.15 mm. Using desired pattern plates, the resist films are patterned to form resist patterns 1120A and 1120B having first opening 1130 and second openings 1140, respectively
10 (FIG. 11(a)).

The first opening 1130 is adapted to etch the lead frame blank 1110 to have a flat etched bottom surface to a thickness smaller than that of the lead frame blank 1110 in a subsequent process. The second openings 1140 are adapted
15 to form desired shapes of tips of inner leads. Although the first opening 1130 includes at least an area forming the tips of the inner leads 1110, a topology generated by partially thinned portion by etching in a subsequent process can cause hindrance in a taping process or a
20 clamping process for fixing the lead frame. Thus, an area to be etched needs to be large without being limited to fine portions of the tips of the inner leads. Thereafter, both surfaces of the lead frame blank 1110 formed with the resist patterns are etched using a 48 Be' ferric chloride
25 solution of a temperature of 57°C at a spray pressure of

2.5 kg/cm². The etching process is terminated at the point of time when first recesses 1150 etched to have a flat etched bottom surface have a depth h corresponding to $1/3$ of the thickness of the lead frame blank (FIG. 11 a).

5 Although both surfaces of the lead frame blank 1110 are simultaneously etched in the primary etching process, it is not necessary to simultaneously etch both surfaces of the lead frame blank 1110. The reason why both surfaces of the lead frame blank 1110 are simultaneously etched, as in
10 this embodiment, is to reduce the etching time taken in a secondary etching process as will be described later. The total time taken for the primary and secondary etching processes is less than that taken in the case of etching of only one surface of the lead frame blank on which the
15 resist pattern 1120B is formed. Subsequently, the surface provided with the first recesses 1150 respectively etched at the first opening 1130 is entirely coated with an etch-resistant hot-melt wax (acidic wax type MR-WB6, The Inctec Inc.) by a die coater to form an etch-resistant
20 layer 1180 so as to fill up the first recesses 1150 and to cover the resist pattern 1120A (FIG. 11(c)).

It is not necessary to coat the etch-resistant layer 1180 over the entire portion of the surface provided with the resist pattern 1120A. However, it is preferred that
25 the etch-resistant layer 1180 be coated over the entire

portion of the surface formed with the first recesses
and first opening 1130, as shown in FIG. 11(c), because
it is difficult to coat the etch-resistant layer 1180 on
the surface portion including the first recesses.
5 Although the etch-resistant layer 1180 was employed in
this embodiment is an alkali-soluble wax, any suitable
material resistant to the etching action of the etchant solution
remaining somewhat soft during etching may be used.

for forming the etch-resistant layer 1180 is not limited
10 to the above-mentioned wax, but may be a wax of a UV-curable
type. Since each first recess 1150 etched by the pre-
etching process at the surface formed with the paste
is adapted to form a desired shape of the inner lead tip,
filled up with the etch-resistant layer 1180, it is
15 further etched in the following secondary etching process.
The etch-resistant layer 1180 also enhances the mechanical
strength of the lead frame blank for the second etching
process, thereby enabling the second etching process to
be conducted while keeping a high accuracy. It is
20 possible to enable a second etchant solution to be sprayed
at an increased spraying pressure, for example, 2.5 kg
or above, in the secondary etching process. The increased
spraying pressure promotes the progress of etching in the
direction of the thickness of the lead frame blank in
25 the secondary etching process. Then, the lead frame blank

subjected to a secondary etching process. In this secondary etching process, the lead frame blank 1110 is etched at its surface formed with first recesses 1130 having a flat etched bottom surface, to completely
5 perforate the second recesses 1160, thereby forming the tips of inner leads 131A (FIG. 11D)).

The bottom surface 1170 of each recess formed by the primary etching process is flat. However, both side surfaces of each recess positioned at opposite sides of the
10 bottom surface 1170 have a concave shape depressed toward the inside of the inner lead. Then, the lead frame blank is cleaned. After completion of the cleaning process, the etch-resistant layer 1180, and resist films (resist patterns 1120A and 1120B) are sequentially removed. Thus,
15 a lead frame 130A having a structure of FIG. 9(a) is obtained in which tips of the inner leads 131A are arranged at a fine pitch. The removal of the etch-resistant layer 1180 and resist films (resist patterns 1120A and 1120B) is achieved using a sodium hydroxide solution serving to
20 dissolve them.

The processes for manufacturing the lead frame as shown in FIG. 11, is to form by means of etching the lead frame having the tips of the inner leads used in this embodiment of the present invention, which have a thickness
25 less than that of the lead frame. Especially, the first

surfaces 131Aa of the tips of the inner leads as shown in
FIG. 1, are flushed with one surfaces of remaining portions
of the inner leads having the same thickness with the lead
frame while being opposed to the second surfaces 131Ab, and
5 the third and fourth surfaces are formed to have a concave
shape which is depressed toward the inside of the inner
leads. Where a semiconductor chip is mounted on the second
surfaces 131Ab of the inner leads by means of bumps for an
electrical connection therebetween, as in a semiconductor
10 device according to a third embodiment as will be described
hereinafter, an increased tolerance for the connection by
bumps is obtained when the second surface 131Ab has a
concave shape depressed toward the inside of the inner
lead. To this end, an etching method shown in FIG. 12 is
15 adopted in this case. The etching method shown in FIG. 12
is the same as that of FIG. 11 in association with its
primary etching process. After completion of the primary
etching process, the etching method is conducted in a
manner different from that of the etching method of FIG. 11
20 in that the second etching process is conducted at the side
of the first recesses 1150 after filling up the second
recesses 1160 by the etch-resist layer 1180, thereby
completely perforating the second recesses 1160. At this
time, by implementing the primary etching process, etching
25 at the side of the second openings 1140 is performed in a

sufficient manner. The cross section of each inner lead, including its tip, formed in accordance with the etching method of FIG. 12, has a concave shape depressed toward the inside of the inner lead at the second surface 131Ab, as shown in FIG. 6(b).

The etching method in which the etching process is conducted at two separate steps, respectively, as in that of FIGs. 11 and 12, is generally called a "two-step etching method". This etching method is advantageous in that a desired fineness can be obtained. The etching method used to fabricate the lead frame 130A of the first embodiment shown in FIG. 9 involves the two-step etching method and the method for forming a desired shape of each lead frame portion while reducing the thickness of each pattern formed. In particular, the etching method makes it possible to achieve a desired fineness. In accordance with the method illustrated in FIGs. 11 and 12, the fineness of the tip of each inner lead 131A formed by this method is dependent on the shape of the second recesses 1160 and the thickness t of the inner lead tip which is finally obtained. For example, where the blank has a thickness t reduced to 50 μ m, the inner leads can have a fineness corresponding to a lead width W_1 of 100 μ m and a tip pitch p of 0.15 mm, as shown in FIG. 11(e). In the case of using a small blank thickness t of about 30 μ m and a lead

width W_1 of 70 μm , it is possible to form inner leads having a fineness corresponding to an inner lead pitch p of 0.12 mm . Of course, it may be possible to form inner leads having a further reduced tip pitch by adjusting the blank thickness t and the lead width W_1 . That is to say, an inner lead tip pitch p up to 0.08 mm , a blank thickness up to 25 μm , and a lead width W_1 up to 40 μm can be obtained.

In the case where twisting of the inner leads does not occur in the fabricating process, as in the case where the inner leads are short in their length, a lead frame illustrated in FIG. 9(a) can be directly obtained. However, where the inner leads are long in length as compared to those of the first embodiment, the inner leads have tendency for the generation of twisting. Thus, in this case, the lead frame is obtained by etching in a state where the tips of the inner leads are bound to each other by a connecting member 131B as shown in FIG. 9(c)(1). Then, the connecting member 131B which is not necessary for the fabrication of a semiconductor package is cut off by means of a press to obtain a lead frame shaped as shown in FIG. 9(a).

Moreover, as described above, where unnecessary portions in a structure shown in FIG. 9(c)(1) are cut to obtain the lead frame having the contour shown in FIG.

9(a), a reinforcing tape 160 (a polyimide tape is generally used, as shown in FIG. 9(b)(A)). While the connecting member 131B is cut off by means of a press to obtain the contour shown in FIG. 9(c)(D), a semiconductor device is mounted on the lead frame still having the reinforcing tape attached thereon. Also, the mounted semiconductor device is encapsulated with a resin in a condition where the lead frame still has the tape. The line E11-E12 illustrates a cut portion.

The tip of the inner lead 131 of the lead frame used in the semiconductor device of this first embodiment has a cross-sectional shape as shown in FIG. 13(1)(a). The tip 131A has an etched flat surface (second surface) 131Ab which is substantially flat and therefore has a width W_1 slightly greater than the width W_2 of an opposite surface. The widths W_1 and W_2 (about 1000 μm) are more than the width W at the central portion of the tips when viewed in the direction of the inner lead thickness. Thus, the tip of the inner lead has a cross-sectional shape having opposite wide surfaces. To this end, although either of the opposite surfaces of the tip 131A can be easily electrically connected to a semiconductor device (not shown) by a wire 120A or 120B, this embodiment illustrates the use of the etched flat surface for wire-bonding as shown in FIG. 13(D)(a). In FIG. 13, a reference numeral

131Ab depicts an etched flat surface, 131Aa a surface of a lead frame blank, and 121A and 121B, respectively, a plated portion. In the case of FIG. 13(D)(a), there has particularly excellent in wire-bonding property, because the etched flat surface does not have roughness. FIG. 13(A) shows that the tip 1331B of the inner lead of the lead frame fabricated according to the process illustrated in FIG. 14 is wire-bonded to a semiconductor device. In this case, however, both the opposite surfaces of the tip 1331B of the inner lead are flat, but have a width smaller than that in a direction of the inner lead thickness. In addition to this, as both the opposite surfaces of the tip 1331B is formed of surfaces of the lead frame blank, these surfaces have an inferior wire-bonding property as compared to that of the etched flat surface of this first embodiment. FIG. 13(B) shows that the inner lead tip 1331C or 1331D, obtained by thinning in its thickness by a means of a press (coining) and then by etching, is wire-bonded to a semiconductor device (not shown). In this case, however, a pressed surface of the inner lead tip is not flat as shown FIG. 13(B). Thus, the wire-bonding on either of the opposite surfaces as shown in FIG. 13(B)(a) or FIG. 13(B)(b) often results in an insufficient wire-bonding stability and a problematic quality. The drawing reference numeral 1331Ab represents a coining surface.

A modified example of the resin-encapsulated semiconductor device in accordance with the first embodiment of the present invention will be described hereinafter. FIGs. 3(a) through 3(e) are cross-sectional views of the modified example of the resin-encapsulated semiconductor device in accordance with the first embodiment of the present invention. The semiconductor device of the modified example as shown in FIG. 3(a), is different from that of the first embodiment in that a position of the die pad 135 is changed, that is, the die pad 135 is exposed to the outside. By the fact that the die pad 135 is exposed to the outside, the heat dissipation property is improved as compared to the first embodiment. Also, in the semiconductor device of the modified example as shown in FIG. 3(b), because the die pad 135 is exposed to the outside, the heat dissipation property is improved as compared to the first embodiment. Unlike the first embodiment or the modified example as shown in FIG. 3(a), in the present modified example as shown in FIG. 3(b), because a direction of the semiconductor device 110 is changed, the first surfaces of the lead frame are established as the wire bonding surfaces. The modified examples as shown in FIGs. 3(c), 3(d) and 3(e), illustrate semiconductor devices which are obtained by modifying the semiconductor devices of the first embodiment, the modified

example as shown in FIG. 3(a) and the modified example as shown in FIG. 3(b), wherein the semi-spherical solders are not used, and instead, the top surfaces of the terminal columns are directly used as the terminal portions, whereby
5 an entire manufacturing procedure can be simplified.

Next, a resin-encapsulated semiconductor device in accordance with a second embodiment of the present invention will be described. FIG. 4(a) is a cross-sectional view of the resin-encapsulated semiconductor device in accordance with the second embodiment of the present invention, FIG. 4(b) is a cross-sectional view illustrating inner leads, taken along the line A3-A4 of FIG. 4(a), and FIG. 4(c) is a cross-sectional view illustrating a terminal column, taken along the line B3-B4 of FIG. 4(a). Because an outer appearance of the semiconductor device of the second embodiment is substantially the same as that of the first embodiment, it is not illustrated in the drawings. In FIG. 3, the drawing reference numeral 200 represents a semiconductor device,
10 210 a semiconductor chip, 211 electrodes (pads), 220 wires, 230 a lead frame, 231 inner leads, 231Ab a second surface, 231Ac a third surface, 231Ad a fourth surface, 233 terminal columns, 233A terminal portions, 233B side surfaces, 233S top surfaces, 240 a resin encapsulate, and 270 a
15 reinforcing fastener tape. In the semiconductor device of
20
25

this second embodiment, the lead frame 230 does not have a die pad, the semiconductor chip 210 is fastened to the inner leads 231 by the reinforcing fastener tape 270, and the semiconductor chip 210 is electrically connected at its electrodes (pads) 211 to the second surfaces 231Ab of the inner leads 231 by wires 220. Also, in the case of this second embodiment, similarly to the first embodiment, the electrical connection between the resin-encapsulated semiconductor device 200 of this embodiment and an external circuit is achieved by mounting the resin-encapsulated semiconductor device 200 via the terminal portions 233A each being made of a semi-spherical solder, on a printed circuit substrate, with the terminal portions 233A located on the top surfaces 233S of the terminal columns 233, respectively.

In addition, the semiconductor device of this second embodiment does not have a die pad as shown in FIGs. 10(a) and 10(b). The manufacturing method of the semiconductor device of this embodiment using the lead frame 230A which is shaped by the etching process is substantially the same as that of the first embodiment except that, while in the case of the first embodiment, the wire bonding process and resin encapsulating process are performed in a state wherein the semiconductor chip is fastened to the inner leads, in the case of the second embodiment, the wire

bonding process and resin encapsulating process are performed in a state wherein the semiconductor chip 210 is fastened together with the inner leads 231 by the reinforcing fastener tape 270. Also, the cutting process for the unnecessary portions and the terminal portion forming process after resin encapsulating process are implemented in the same way as the first embodiment. The lead frame 230 as shown in FIG. 10(a) is obtained in the same manner by which the lead frame 130A as shown in FIG. 9(a) is obtained. In other words, by cutting the resultant structure obtained after etching the structure as shown in FIG. 10(c)(1), the contour as shown in FIG. 10(a) is obtained. At this time, the conventional reinforcing fastener tape 260 (the polyimide tape) as shown in FIG. 10(c)(2), which performs a reinforcing function is used.

FIG. 5(a) through 5(c) are cross-sectional views illustrating modified examples of the semiconductor device of the second embodiment. The semiconductor device as shown in FIG. 5(a) is different from the semiconductor device of the second embodiment, in that the surface of the semiconductor chip thereof which has the electrodes is directed downward. The modified examples as shown in FIGS. 5(b) and 5(c), illustrate semiconductor devices which are obtained by modifying the semiconductor devices of the second embodiment and the modified example as shown in FIG.

5(a), wherein the semi-spherical solders are not used, and instead, the top surfaces of the terminal columns are directly used as the terminal portions. In these examples, because a protective frame is not used and the side surfaces 333B of the terminal columns 333 are exposed to the outside, a checking operation by a test, etc. can be easily performed.

Hereinafter, a resin-encapsulated semiconductor device in accordance with a third embodiment of the present invention will be described. FIG. 6(a) is a cross-sectional view of the resin-encapsulated semiconductor device of the third embodiment, FIG. 6(b) is a cross-sectional view illustrating inner leads, taken along the line A5-A6 of FIG. 6(a), and FIG. 6(c) is a cross-sectional view illustrating a terminal column, taken along the line B5-B6 of FIG. 6(b). Because an outer appearance of the semiconductor device of the this third embodiment is substantially the same as that of the first embodiment, it is not illustrated in the drawings. In FIG. 6, the drawing reference numeral 300 represents a semiconductor device, 310 a semiconductor chip, 312 bumps, 330 a lead frame, 331 inner leads, 331Aa a first surface, 331Ab a second surface, 331Ac a third surface, 331Ad a fourth surface, 333 terminal columns, 333A terminal portions, 333B side surfaces, 333S top surfaces, 340 a resin encapsulate, and 350 a

reinforcing fastener tape. In the semiconductor device of this third embodiment, the semiconductor chip 310 is fastened to the second surfaces 331Ab of the inner leads 331 by the bumps 311 thereby to be electrically connected to the second surfaces 331Ab. The lead frame 330 has a contour as shown in FIGs. 10(a) and 10(b), which is formed by the etching process of FIG. 11. As shown in FIG. 13(1)(b), both widths W1A and W2A (about 100 μ m) at top and bottom ends of the inner leads 331 are larger than a width WA at a center portion in a thickness-wise direction. Due to the fact that the second surfaces 331Ab of the inner leads 331 is depressed toward the inside of the inner leads and the first surfaces 331Aa are flat, a desired fineness can be obtained. Also, when the second surfaces 331Ab of the inner leads 331 are electrically connected to the semiconductor chip via bumps, easy connection can be accomplished as shown in FIG. 13(2)(b). Further, in the case of this third embodiment, as in the case of the first and second embodiments, the electrical connection between the resin-encapsulated semiconductor device 300 of this embodiment and an external circuit is achieved by mounting the resin-encapsulated semiconductor device 300 via the terminal portions 333A each being made of a semi-spherical solder, on a printed circuit substrate, with the terminal portions 333A located on the top surfaces of the terminal

columns 333, respectively.

In addition, unlike the semiconductor device of the first embodiment, the semiconductor device of this third embodiment uses a lead frame which is shaped by the etching process as shown in FIG. 12. However, the manufacturing method of the semiconductor device of this embodiment is substantially the same as that of the first embodiment except that, while in the case of the first embodiment, the wire bonding process and resin encapsulating process are performed in a state wherein the semiconductor chip is fastened to the inner leads, in the case of this third embodiment, the wire bonding process and resin encapsulating process are performed in a state wherein the semiconductor chip 310 is fastened to the inner leads 331 via the bumps. Also, the cutting process for the unnecessary portions and the terminal portion forming process after resin encapsulating process are implemented in the same way as the first embodiment.

FIG. 6(d) is a cross-sectional view illustrating a modified example of the semiconductor device in accordance with the third embodiment of the present invention. In the modified example of the semiconductor device as shown in FIG. 6(d), the terminal portions each comprising the semi-spherical solder are not provided, and the top surfaces of the terminal columns are directly used as the terminal

portions. Because the protective frame is not used and the side surfaces 333B of the terminal columns 333 are exposed to the outside, a checking operation by a test, etc. can be easily performed.

5 Hereinafter, a resin-encapsulated semiconductor device in accordance with a fourth embodiment of the present invention will be described. FIG. 7(a) is a cross-sectional view of the resin-encapsulated semiconductor device of the fourth embodiment, FIG. 7(b) is a cross-sectional view illustrating inner leads, taken along the line A7-A8 of FIG. 7(a), and FIG. 7(c) is a cross-sectional view illustrating a terminal column, taken along the line 10 37-38 of FIG. 7(b). Because an outer appearance of the semiconductor device of the this fourth embodiment is substantially the same as that of the first embodiment, it is not illustrated in the drawings. In FIG. 7, the drawing 15 reference numeral 400 represents a semiconductor device, 410 a semiconductor chip, 411 pads, 430 a lead frame, 431 inner leads, 431Aa a first surface, 431Ab a second surface, 431Ac a third surface, 431Ad a fourth surface, 433 terminal columns, 433A terminal portions, 433B side surfaces, 433S top surfaces, 440 a resin encapsulate, and 470 insulating 20 adhesive. In the semiconductor device of this fourth embodiment, one surface of the semiconductor chip 410 on which the pads 411 are disposed is fastened to the second 25

surfaces 431Ab of the inner leads 431 by the insula
adhesive 470, and the pads 411 and the first surfaces
of the inner leads 431 are electrically connected with
other by wires 420. The semiconductor device of
5 fourth embodiment uses the same lead frame which is use
the third embodiment, which has the contour as shown
FIG. 10(a) and 10(b). Also, in the case of this fourth
embodiment, as in the case of the first and second
embodiments, the electrical connection between the res
10 encapsulated semiconductor device 400 of this embodiment
and an external circuit is achieved by mounting the res
encapsulated semiconductor device 400 via the terminal
portions 433A each being made of a semi-spherical solder
on a printed circuit substrate, with the terminal portion
15 433A located on the top surfaces of the terminal columns
433, respectively.

FIG. 7(d) is a cross-sectional view illustrating
modified example of the semiconductor device in accordance
with the fourth embodiment of the present invention. In
20 the modified example of the semiconductor device as shown
in FIG. 7(d), the terminal portions each comprising the
semi-spherical solder are not provided, and the top
surfaces of the terminal columns are directly used as the
terminal portions. Because the protective frame is not
25 used and the side surfaces 433B of the terminal columns 433

are exposed to the outside, a checking operation by a test, etc. can be easily performed.

{EFFECTS OF THE INVENTION}

5 The present invention provides a resin-encapsulated semiconductor device employing the above-mentioned lead frame, which is capable of meeting a demand for the increased terminal number. Furthermore, the resin-encapsulated semiconductor device in accordance with this invention does not require a process of cutting or bending
10 the dam bars as in the case of using a lead frame having outer leads as shown in FIG. 13(b). As a result of this, the resin-encapsulated semiconductor device does not have a problem in that the outer leads are bent, or a problem
15 associated with coplanarity. In addition to these advantages, the resin-encapsulated semiconductor device has a shortened interconnection length as compared to the QTP or the BGA, whereby the semiconductor device can be reduced in a parasitic capacity, and shortened in a transfer delay
20 time.

59:543 v: